

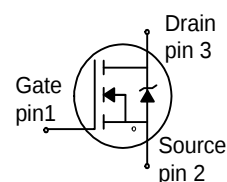
OptiMOS[®] Buck converter series
Feature

- N-Channel
- Enhancement mode
- Logic Level
- Avalanche rated ¹⁾
- Pb-free lead plating; RoHS compliant
- Qualified according to AEC Q101
- Halogen-free according to IEC61249-2-21


Product Summary

V_{DS}	55	V
$R_{DS(on)}$	650	m Ω
I_D	0.54	A

PG-SOT 23



Type	Package	Tape and Reel	Marking
BSS670S2L	PG-SOT 23	H6327: 3000 pcs/reel	BSS

Maximum Ratings, at $T_j = 25\text{ }^{\circ}\text{C}$, unless otherwise specified

Parameter	Symbol	Value	Unit
Continuous drain current $T_A = 25^{\circ}\text{C}$ $T_A = 70^{\circ}\text{C}$	I_D	0.54 0.43	A
Pulsed drain current $T_A = 25^{\circ}\text{C}$	$I_{D\text{ puls}}$	2.2	
Avalanche energy, single pulse $I_D = 0.54\text{ A}$, $R_G = 25\text{ }\Omega$ ¹⁾	E_{AS}	8.1	mJ
Gate source voltage	V_{GS}	± 20	V
Power dissipation $T_A = 25^{\circ}\text{C}$	P_{tot}	0.36	W
Operating and storage temperature	T_j, T_{stg}	-55... +150	$^{\circ}\text{C}$
IEC climatic category; DIN IEC 68-1		55/150/56	
ESD Class JESD22-A114-HBM		Class 0	

¹⁾ Valid from devices with date code 0604 onwards

Thermal Characteristics

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Characteristics					
Thermal resistance, junction - soldering point (Pin 3)	R_{thJS}	-	-	290	K/W
SMD version, device on PCB:	R_{thJA}				
@ min. footprint		-	-	350	
@ 6 cm ² cooling area 2)		-	-	300	

Electrical Characteristics, at $T_j = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Static Characteristics					
Drain-source breakdown voltage $V_{GS}=0, I_D=1\text{mA}$	$V_{(BR)DSS}$	55	-	-	V
Gate threshold voltage, $V_{GS} = V_{DS}$ $I_D=2.7\mu\text{A}$	$V_{GS(th)}$	1.2	1.6	2	
Zero gate voltage drain current $V_{DS}=55\text{V}, V_{GS}=0, T_j=25^\circ\text{C}$ $V_{DS}=55\text{V}, V_{GS}=0, T_j=150^\circ\text{C}$	I_{DSS}	- -	0.01 1	0.1 10	μA
Gate-source leakage current $V_{GS}=20\text{V}, V_{DS}=0\text{V}$	I_{GSS}	-	1	100	
Drain-source on-state resistance $V_{GS}=4.5\text{V}, I_D=270\text{mA}$	$R_{DS(on)}$	-	430	825	$\text{m}\Omega$
Drain-source on-state resistance $V_{GS}=10\text{V}, I_D=270\text{mA}$	$R_{DS(on)}$	-	346	650	

²⁾ Device on 40mm*40mm*1.5mm epoxy PCB FR4 with 6cm² (one layer, 70 μm thick) copper area for drain connection. PCB is vertical without blown air.

Electrical Characteristics

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

Dynamic Characteristics

Transconductance	g_{fs}	$V_{DS} \geq 2 \cdot I_D \cdot R_{DS(on)max}$, $I_D = 0.54A$	0.6	1.2	-	S
Input capacitance	C_{iss}	$V_{GS} = 0$, $V_{DS} = 25V$, $f = 1MHz$	-	56	75	pF
Output capacitance	C_{oss}		-	13	18	
Reverse transfer capacitance	C_{rss}		-	7	10	
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 30V$, $V_{GS} = 4.5V$, $I_D = 0.54A$, $R_G = 130\Omega$	-	9	14	ns
Rise time	t_r		-	25	37	
Turn-off delay time	$t_{d(off)}$		-	21	31	
Fall time	t_f		-	24	32	

Gate Charge Characteristics

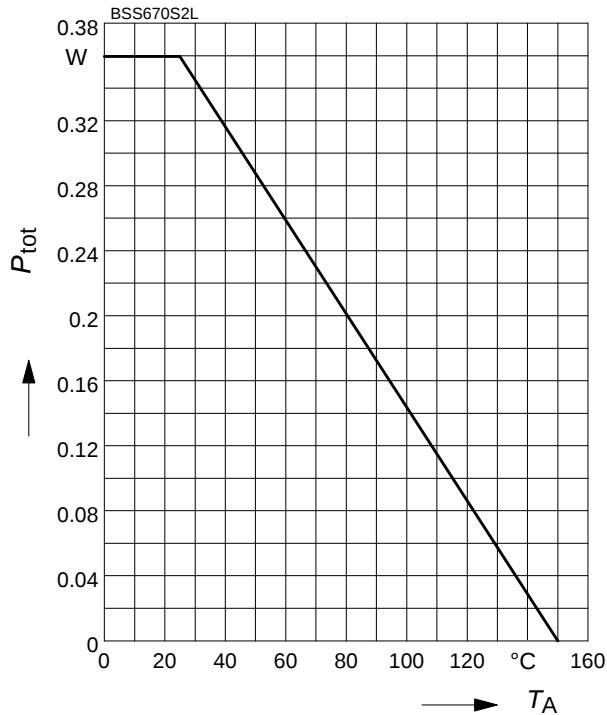
Gate to source charge	Q_{gs}	$V_{DD} = 40V$, $I_D = 0.54A$	-	0.19	0.25	nC
Gate to drain charge	Q_{gd}		-	0.57	0.86	
Gate charge total	Q_g	$V_{DD} = 40V$, $I_D = 0.54A$, $V_{GS} = 0$ to $10V$	-	1.7	2.26	
Gate plateau voltage	$V_{(plateau)}$	$V_{DD} = 40V$, $I_D = 0.54A$	-	3.1	-	V

Reverse Diode

Inverse diode continuous forward current	I_S	$T_A = 25^\circ C$	-	-	0.38	A
Inv. diode direct current, pulsed	I_{SM}		-	-	2.2	
Inverse diode forward voltage	V_{SD}	$V_{GS} = 0$, $I_F = 0.54A$	-	0.8	1.1	V
Reverse recovery time	t_{rr}	$V_R = 30V$, $I_F = I_S$, $di_F/dt = 100A/\mu s$	-	51	64	ns
Reverse recovery charge	Q_{rr}		-	22	28	nC

1 Power dissipation

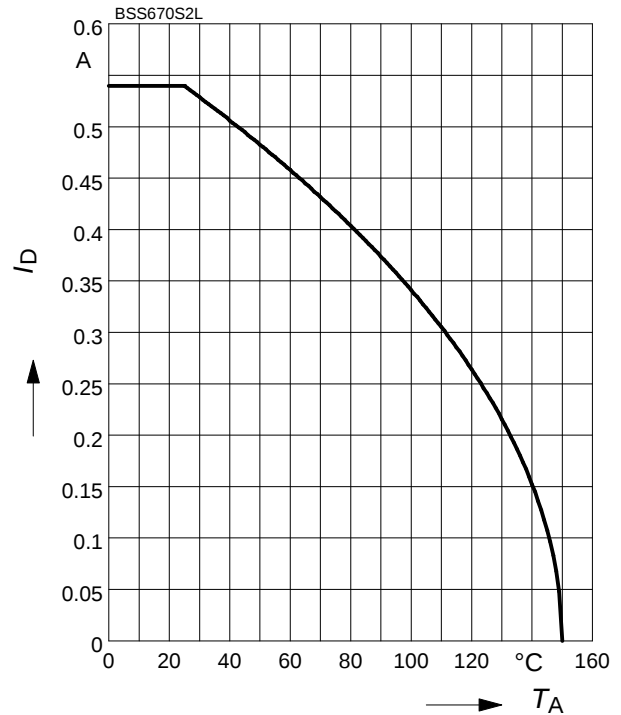
$$P_{\text{tot}} = f(T_A)$$



2 Drain current

$$I_D = f(T_A)$$

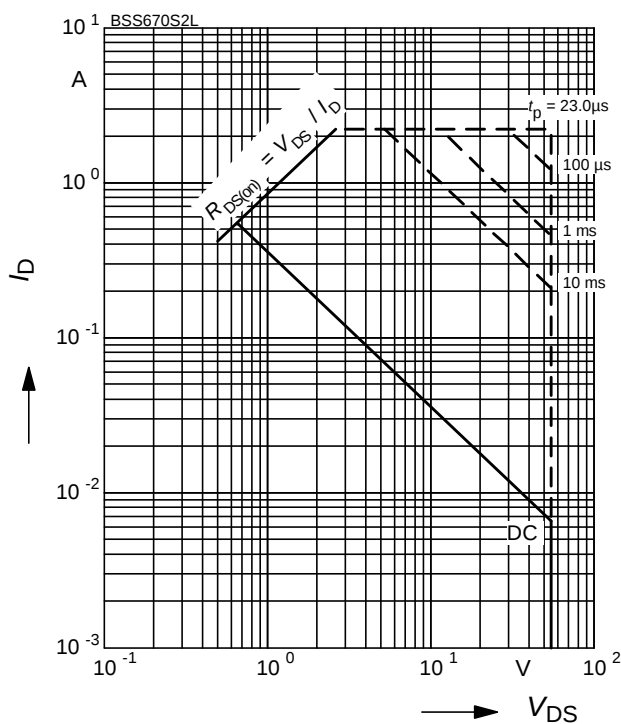
parameter: $V_{GS} \geq 10 \text{ V}$



3 Safe operating area

$$I_D = f(V_{DS})$$

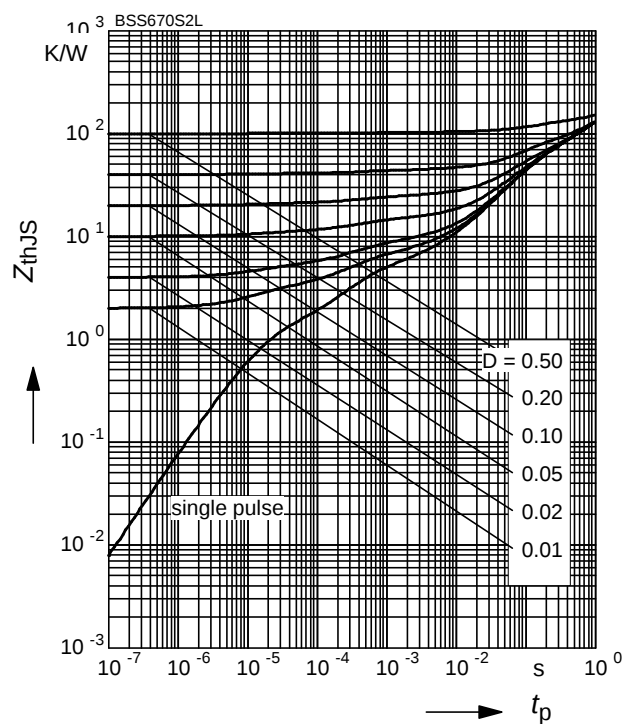
parameter: $D = 0$, $T_A = 25^\circ\text{C}$



4 Transient thermal impedance

$$Z_{\text{thJS}} = f(t_p)$$

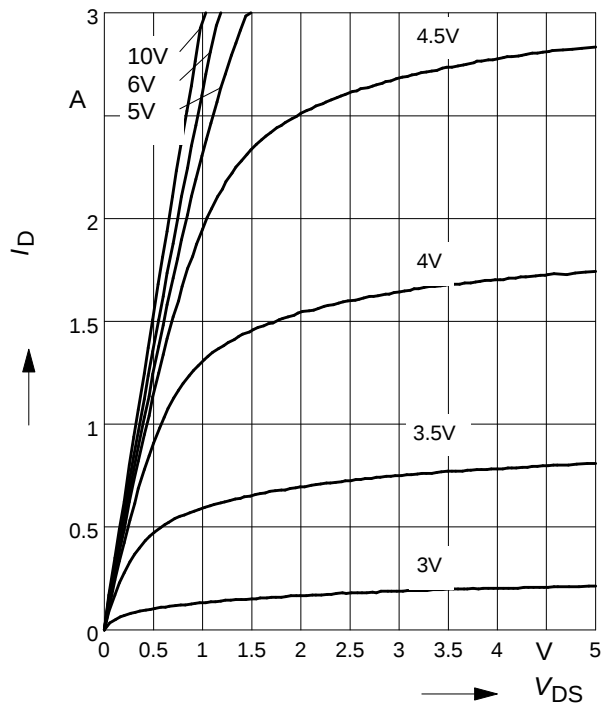
parameter: $D = t_p / T$



5 Typ. output characteristic

$I_D = f(V_{DS})$; $T_j = 25^\circ\text{C}$

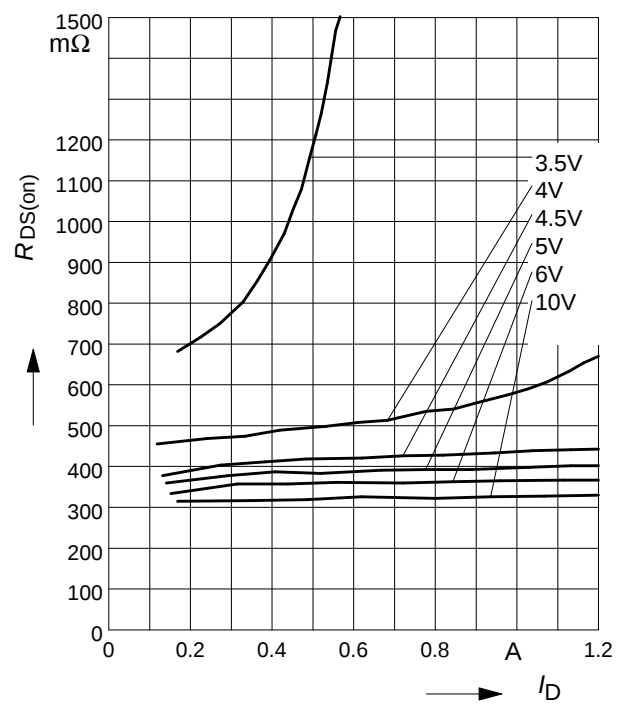
parameter: $t_p = 80\ \mu\text{s}$



6 Typ. drain-source on resistance

$R_{DS(on)} = f(I_D)$

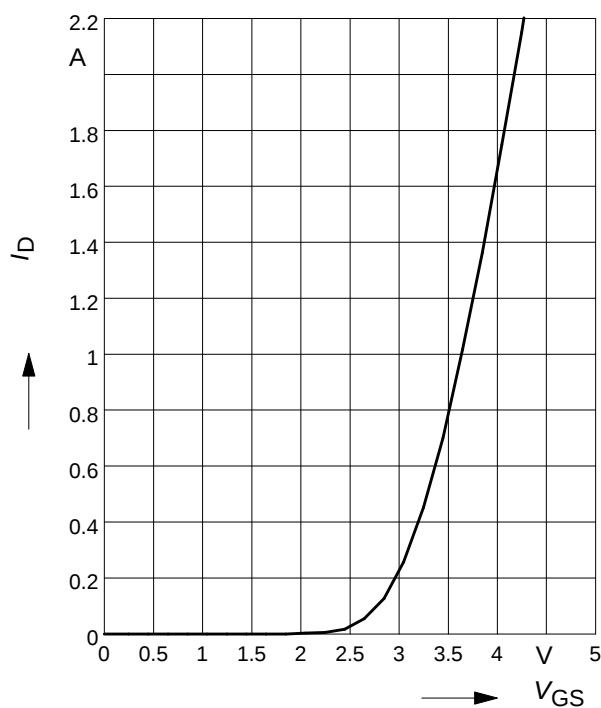
parameter: V_{GS}



7 Typ. transfer characteristics

$I_D = f(V_{GS})$; $V_{DS} \geq 2 \times I_D \times R_{DS(on)max}$

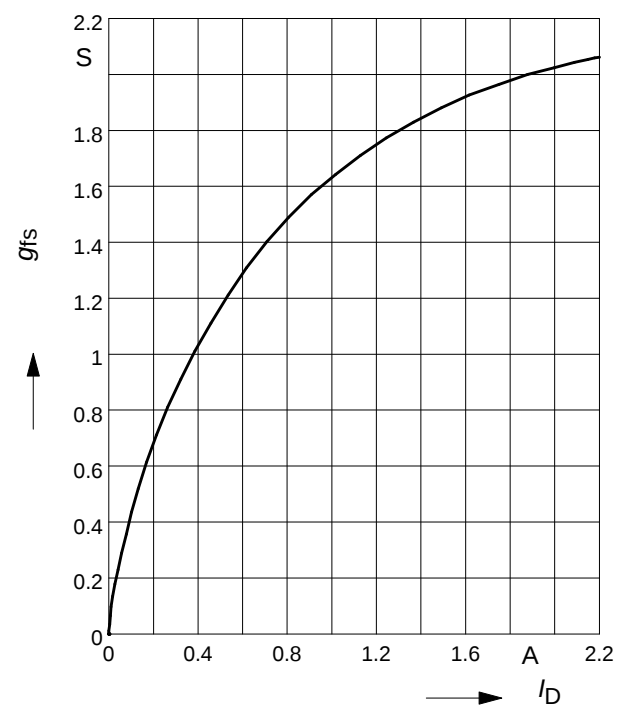
parameter: $t_p = 80\ \mu\text{s}$



8 Typ. forward transconductance

$g_{fs} = f(I_D)$; $T_j = 25^\circ\text{C}$

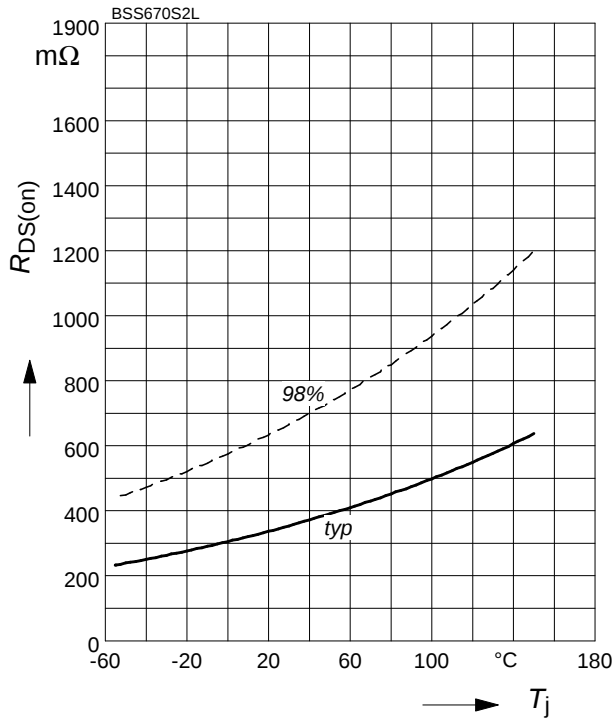
parameter: g_{fs}



9 Drain-source on-state resistance

$$R_{DS(on)} = f(T_j)$$

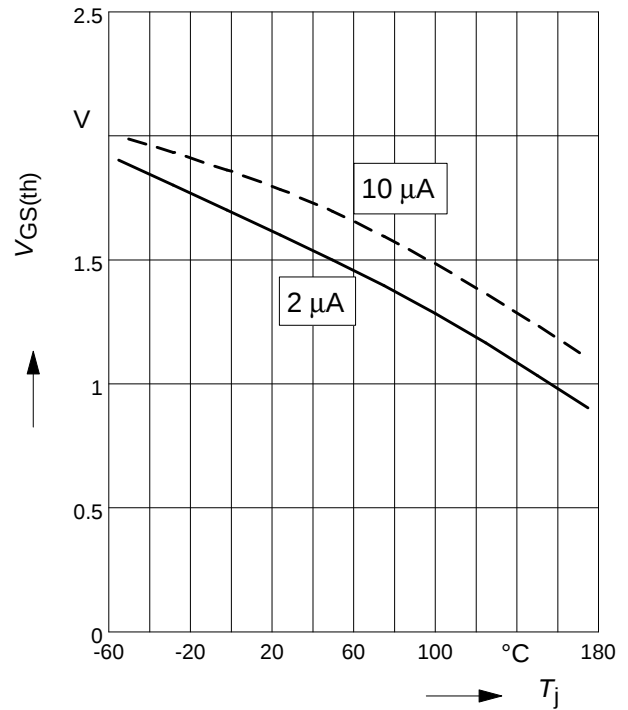
parameter: $I_D = 270 \text{ mA}$, $V_{GS} = 10 \text{ V}$



10 Typ. gate threshold voltage

$$V_{GS(th)} = f(T_j)$$

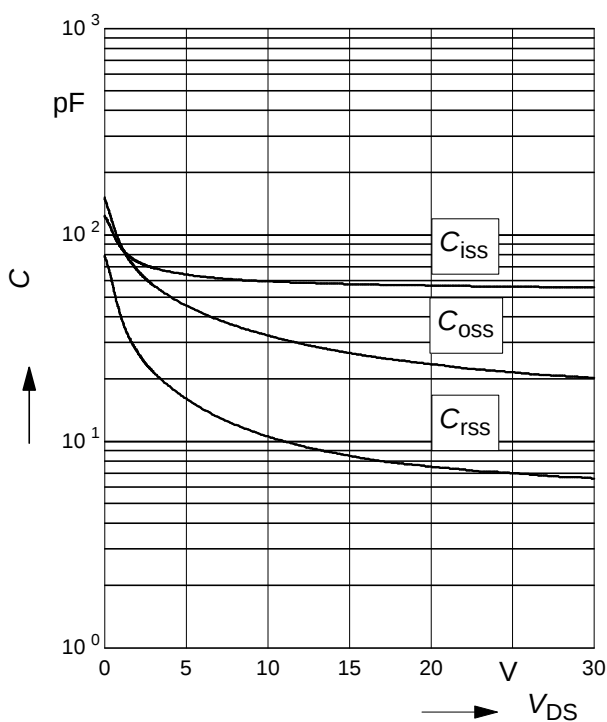
parameter: $V_{GS} = V_{DS}$



11 Typ. capacitances

$$C = f(V_{DS})$$

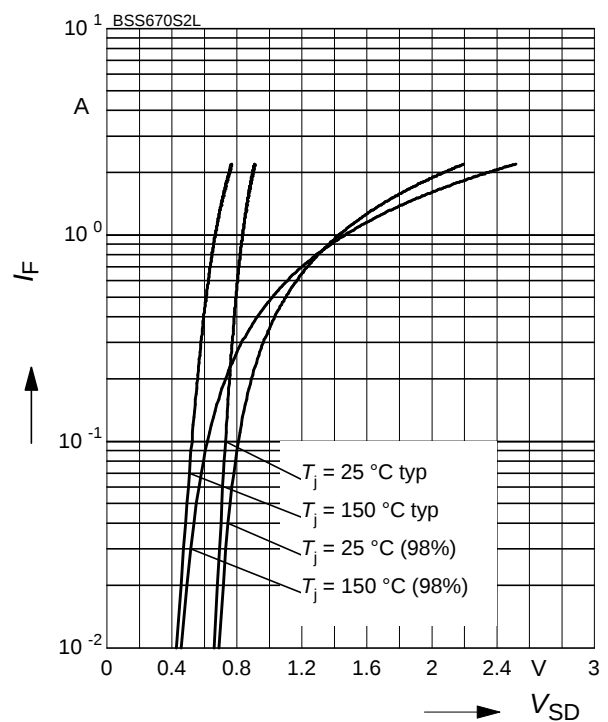
parameter: $V_{GS}=0$, $f=1 \text{ MHz}$



12 Forward character. of reverse diode

$$I_F = f(V_{SD})$$

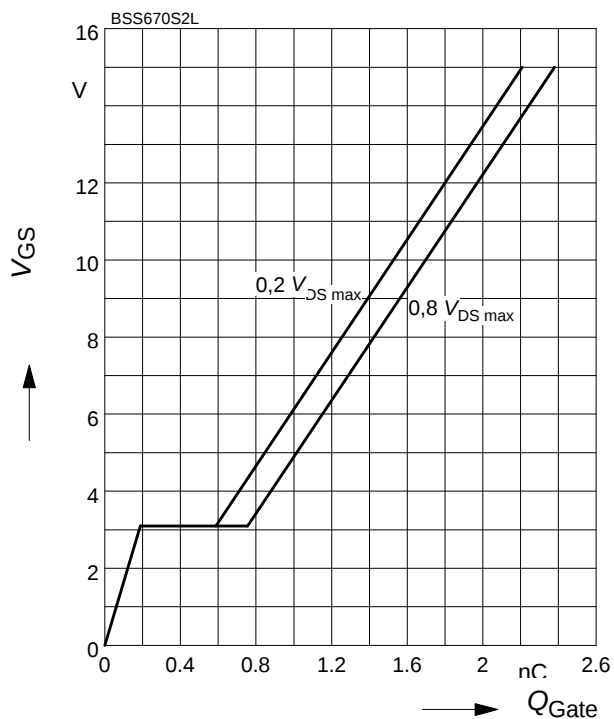
parameter: T_j , $t_p = 80 \mu\text{s}$



13 Typ. gate charge

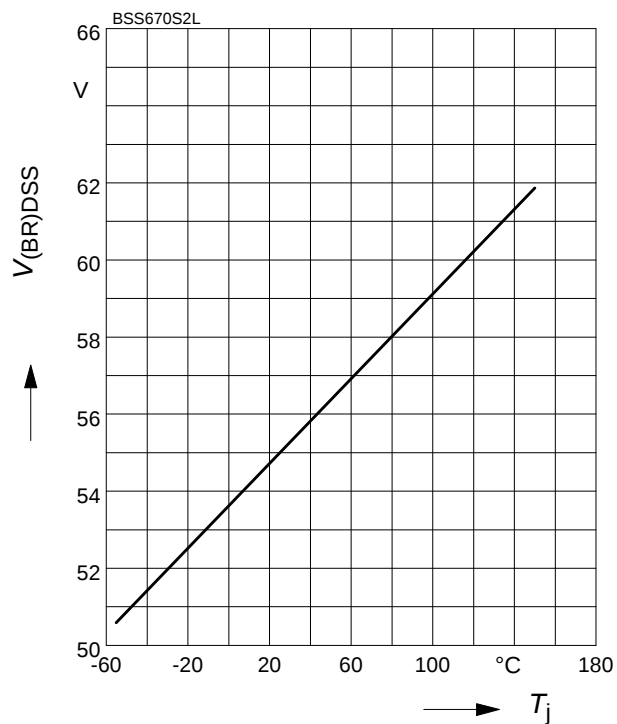
$$V_{GS} = f(Q_{Gate})$$

parameter: $I_D = 0.54$ A pulsed


14 Drain-source breakdown voltage

$$V_{(BR)DSS} = f(T_j)$$

parameter: $I_D = 10$ mA



Published by
Infineon Technologies AG
81726 Munich, Germany
© 2010 Infineon Technologies AG
All Rights Reserved.

Legal Disclaimer

The information given in this document shall in no event be regarded as a guarantee of conditions or characteristics. With respect to any examples or hints given herein, any typical values stated herein and/or any information regarding the application of the device, Infineon Technologies hereby disclaims any and all warranties and liabilities of any kind, including without limitation, warranties of non-infringement of intellectual property rights of any third party.

Information

For further information on technology, delivery terms and conditions and prices, please contact the nearest Infineon Technologies Office (www.infineon.com).

Warnings

Due to technical requirements, components may contain dangerous substances. For information on the types in question, please contact the nearest Infineon Technologies Office.

Infineon Technologies components may be used in life-support devices or systems only with the express written approval of Infineon Technologies, if a failure of such components can reasonably be expected to cause the failure of that life-support device or system or to affect the safety or effectiveness of that device or system. Life support devices or systems are intended to be implanted in the human body or to support and/or maintain and sustain and/or protect human life. If they fail, it is reasonable to assume that the health of the user or other persons may be endangered.

Данный компонент на территории Российской Федерации

Вы можете приобрести в компании MosChip.

Для оперативного оформления запроса Вам необходимо перейти по данной ссылке:

<http://moschip.ru/get-element>

Вы можете разместить у нас заказ для любого Вашего проекта, будь то серийное производство или разработка единичного прибора.

В нашем ассортименте представлены ведущие мировые производители активных и пассивных электронных компонентов.

Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

Офис по работе с юридическими лицами:

105318, г.Москва, ул.Щербаковская д.3, офис 1107, 1118, ДЦ «Щербаковский»

Телефон: +7 495 668-12-70 (многоканальный)

Факс: +7 495 668-12-70 (доб.304)

E-mail: info@moschip.ru

Skype отдела продаж:

moschip.ru

moschip.ru_4

moschip.ru_6

moschip.ru_9